

**SuperMOS – SOT-23 -30V  $BV_{DSS}$ , 46m $\Omega$   $R_{DS(on)}$ , P-channel MOSFET**

**1. Description**

The LP3407LT1G-ES is P-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product LP3407LT1G-ES is Pb-free.

**2. Features**

- 30V,  $R_{DS(ON)}=46m\Omega$ (Typ.) @ $V_{GS}=-10V$   
 $R_{DS(ON)}=62m\Omega$ (Typ.) @ $V_{GS}=-4.5V$
- Fast Switching
- High density cell design for low  $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

**3. Applications**

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

**4. Ordering Information**

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
LP3407LT1G-ES	SOT-23	R7	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

Table-1 Ordering information

**5. Pin Configuration and Functions**

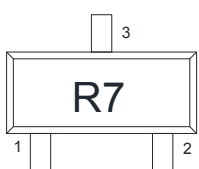
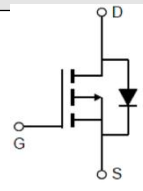
Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

Table-2 Pin configuration

## 6. Specification

### Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$BV_{DSS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_A=25^\circ\text{C}$	-3.8
		$T_A=75^\circ\text{C}$	-2.9
Maximum Power Dissipation	$P_D$	1.4	W
Pulsed Drain Current	$I_{DM}$	-15.2	A
Operating Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

#### Thermal resistance ratings

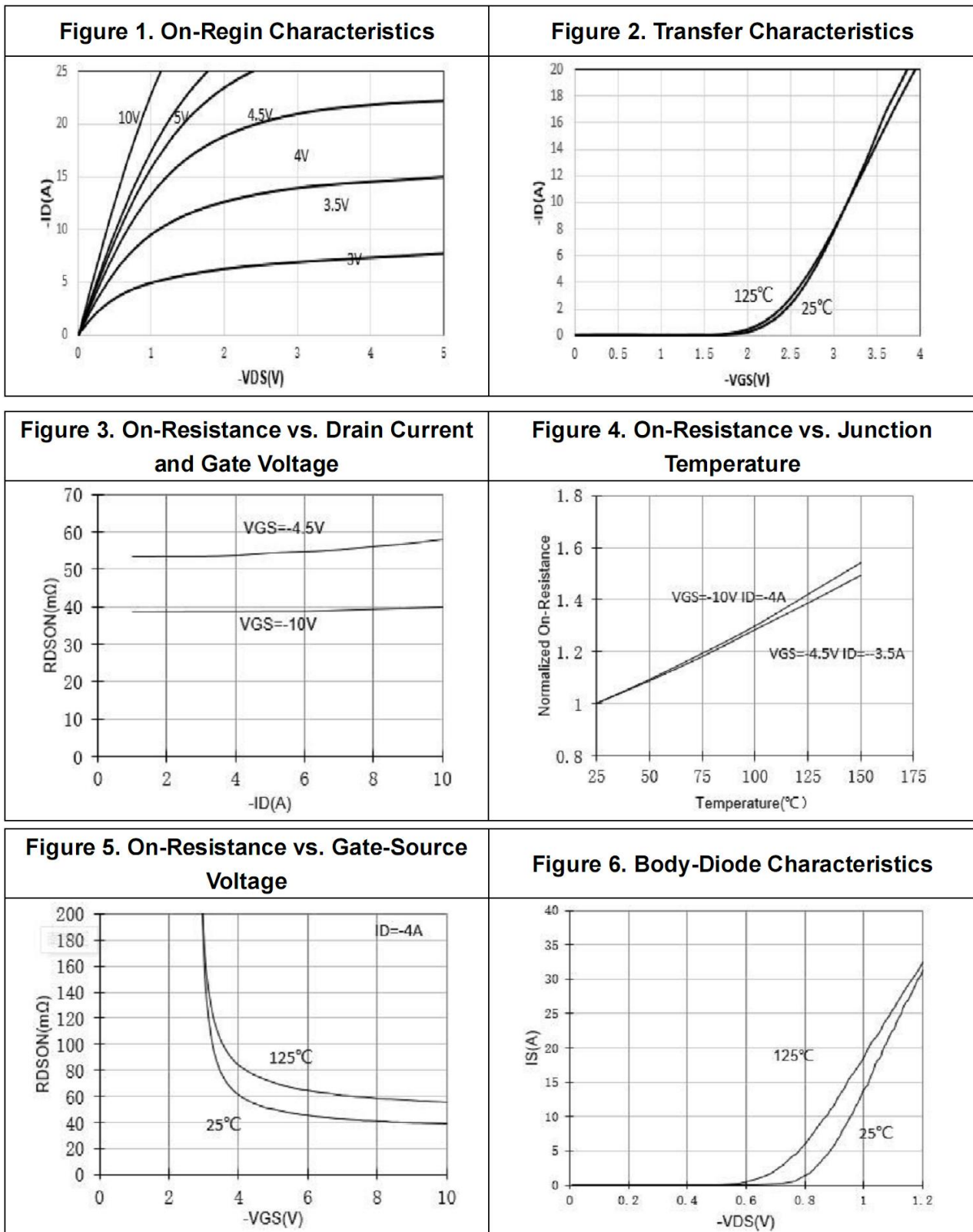
Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$		90	$^\circ\text{C/W}$

## Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$			-1	$\mu A$
Gate-to-source Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.9	-1.5	-2.0	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-3A$		46	60	m $\Omega$
		$V_{GS}=-4.5V, I_D=-3A$		62	80	
<b>CHARGES, CAPACITANCES AND GATE RESISTANCE</b>						
Input Capacitance	$C_{ISS}$	$V_{GS}=0V, V_{DS}=-15V,$ $f=1MHz$		550		pF
Output Capacitance	$C_{OSS}$			75		
Reverse Transfer Capacitance	$C_{RSS}$			63		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=-10V, V_{DS}=-15V,$ $I_D=-4A$		6.5		nC
Gate-to-Source Charge	$Q_{GS}$			1.1		
Gate-to-Drain Charge	$Q_{GD}$			1.3		
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=-10V, V_{DS}=-15V,$ $R_L=3.5\Omega, R_G=3\Omega$		14		ns
Rise Time	$t_r$			60		
Turn-Off Delay Time	$t_{d(OFF)}$			19		
Fall Time	$t_f$			11		
<b>BODY DIODE CHARACTERISTICS</b>						
Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=-1.0A$		-0.7	-1.5	V

7. Typical Characteristic



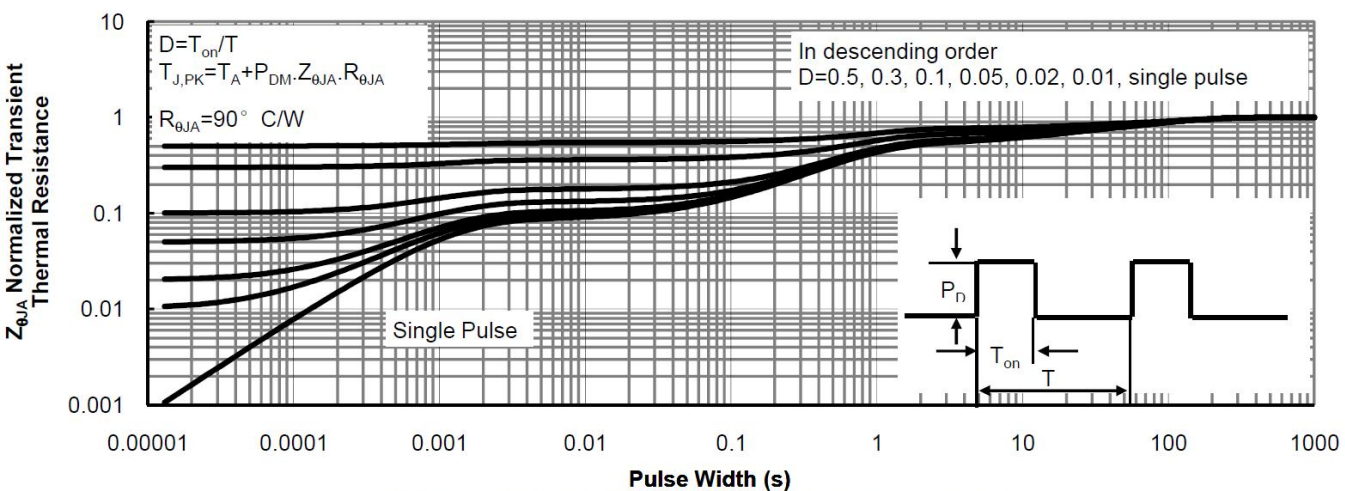
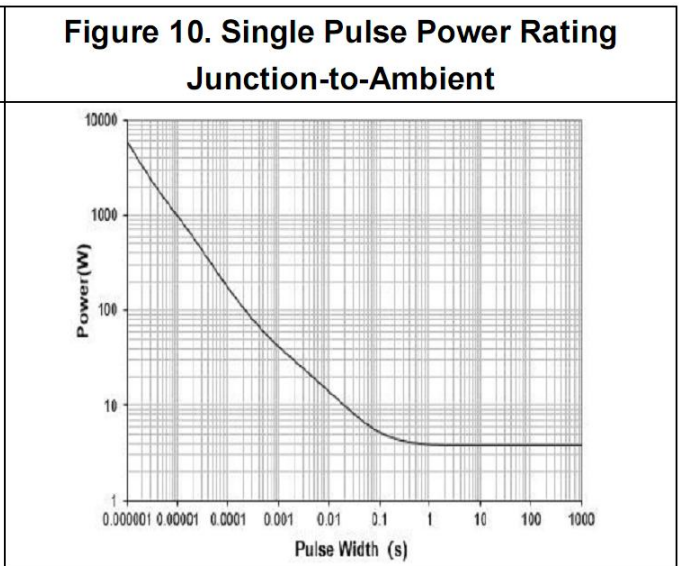
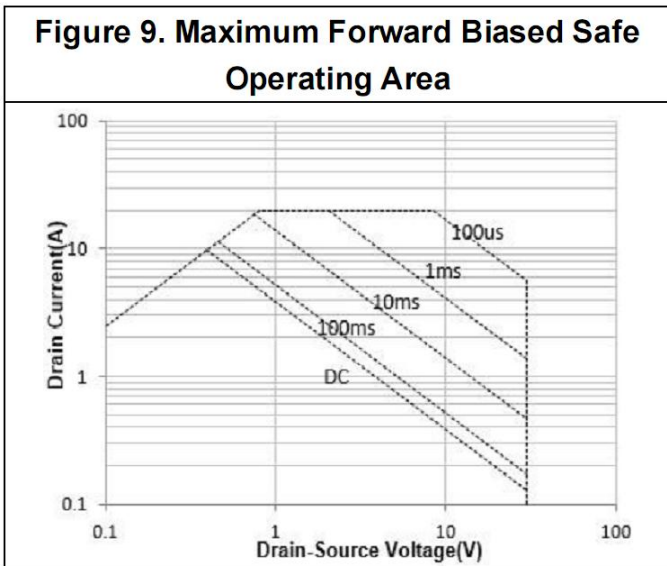
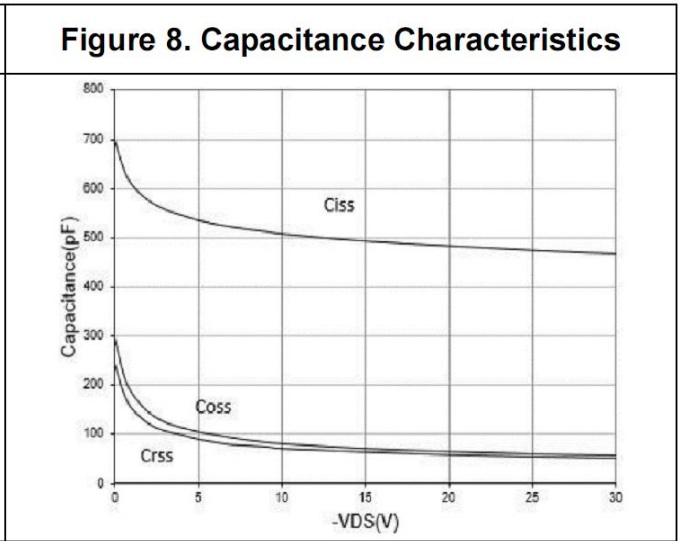
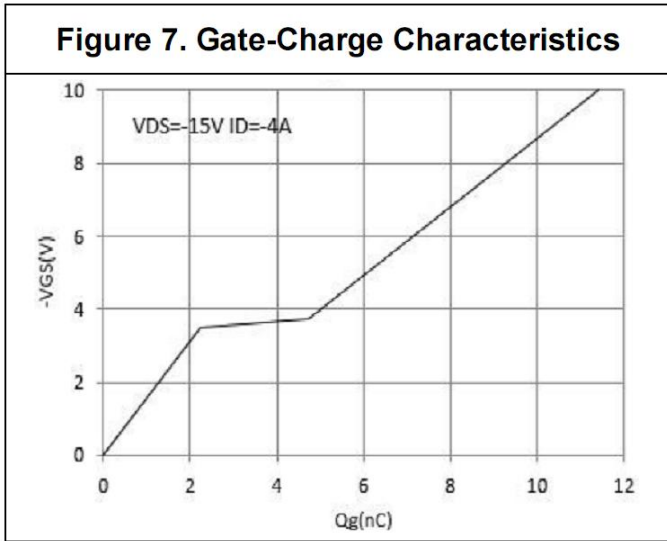
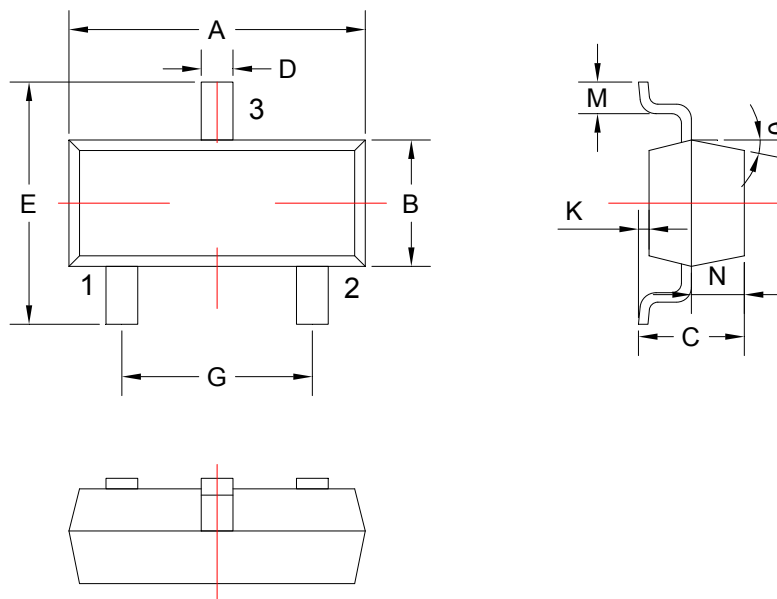


Figure 11: Normalized Maximum Transient Thermal Impedance

8. Dimension (SOT-23)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.85	3.04	G	1.80	2.00
B	1.20	1.40	K	0	0.10
C	0.90	1.10	M	0.20	-
D	0.40	0.50	N	0.50	0.70
E	2.25	2.55	θ	5°	9°

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